

Supporting Information

Efficient emission quasi-two-dimensional perovskite films casted by ink-jet printing for pixel-defined matrix light-emitting diodes

Junjie Wang¹, Danyang Li¹, Jian Wang¹, Junbiao Peng^{1,*}

¹Institute of Polymer Optoelectronic Materials and Devices, State Key Laboratory of Luminescent Materials and Devices, South China University of Technology, Guangzhou 510640, China.

* E-Mail: psjbpeng@scut.edu.cn

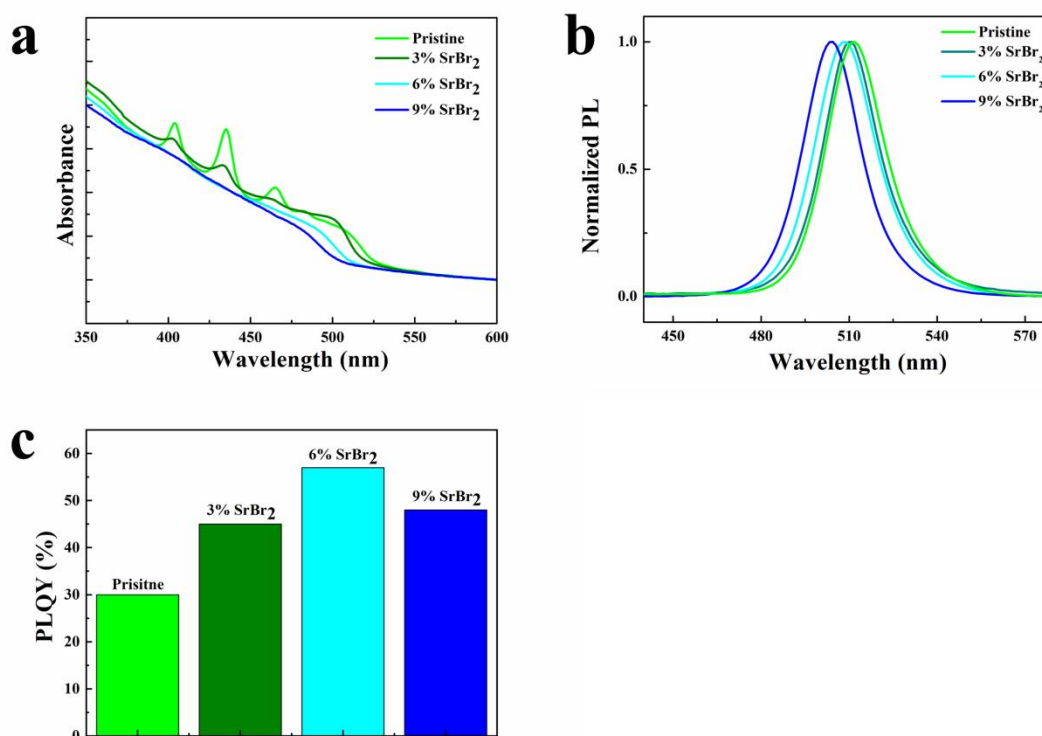


Figure S1. (a) Absorption spectra, (b) PL spectra and (c) PLQY of perovskite films with different SrBr₂ proportions.

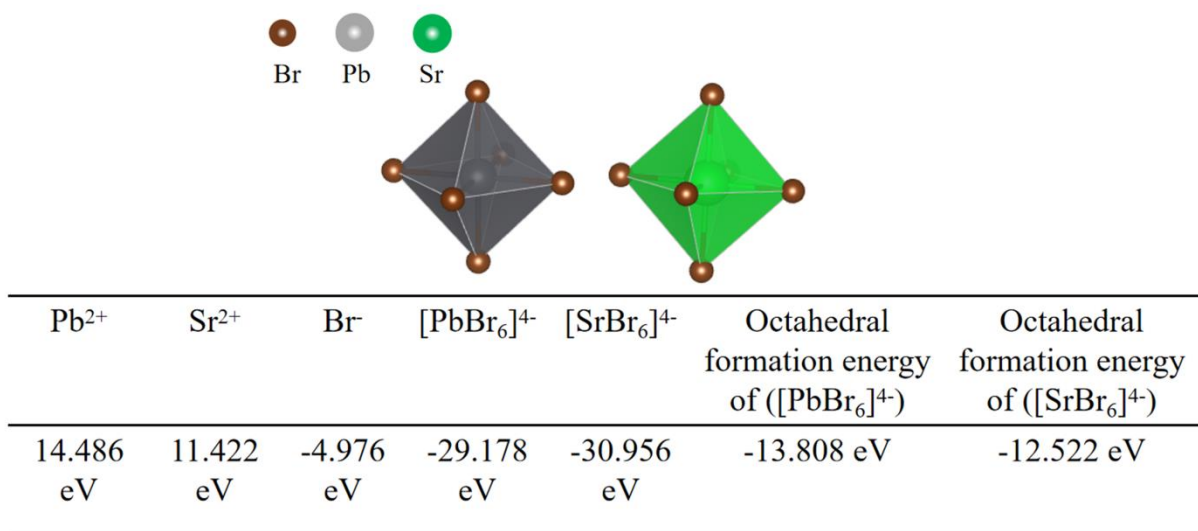


Figure S2. Octahedral formation energy calculation results of [PbBr₆]⁴⁻ and [SrBr₆]⁴⁻ by DFT.

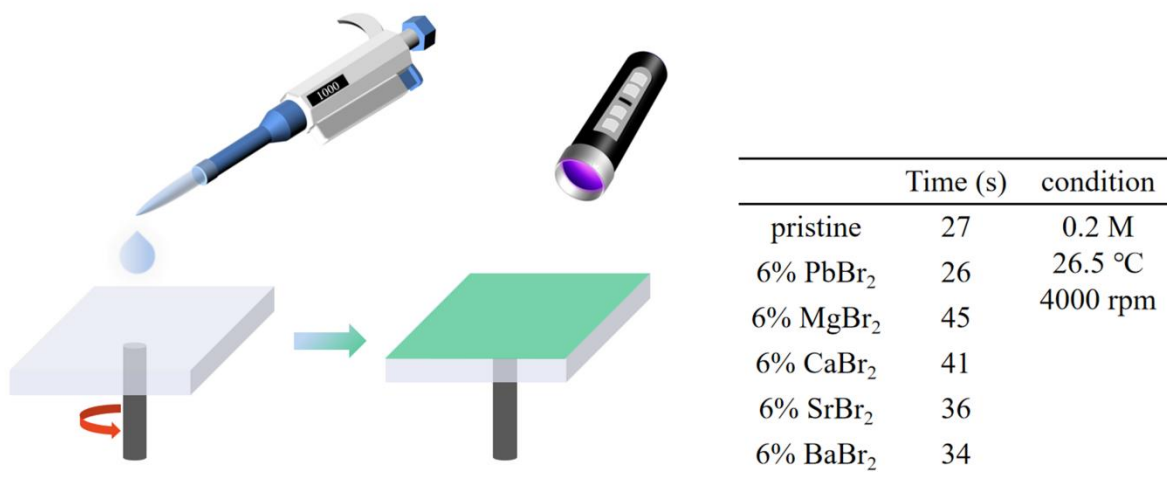


Figure S3. Schematic illustration of the spin-coating process for perovskite films on quartz substrate and crystallizing time.

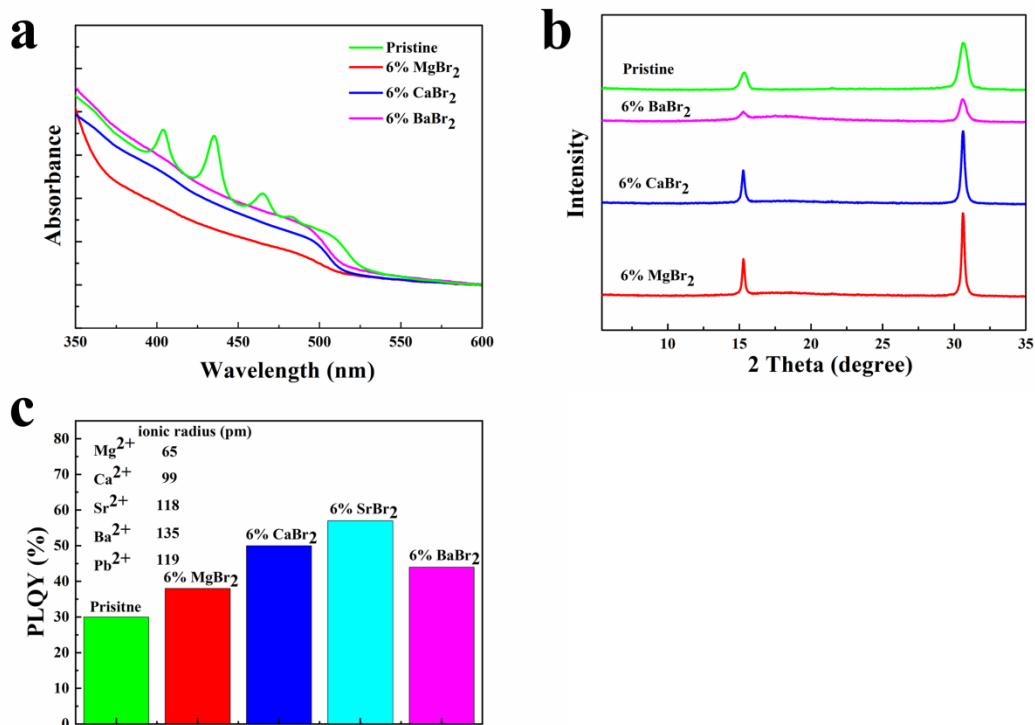


Figure S4. (a) Absorption spectra of quasi-2D perovskite films with 6% MgBr₂, 6% CaBr₂, 6% BaBr₂, (b) XRD spectra of quasi-2D perovskite films with 6% MgBr₂, 6% CaBr₂, 6% BaBr₂, (c) PLYQ of quasi-2D perovskite films with 6% MgBr₂, 6% CaBr₂, 6% SrBr₂, 6% BaBr₂.

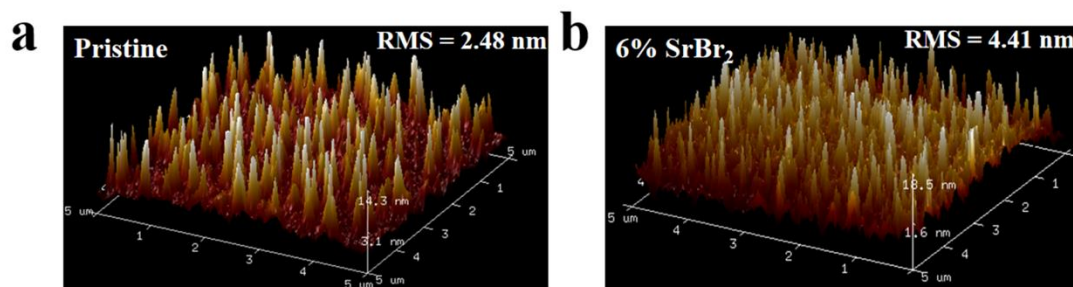


Figure S5. Atomic force microscope images of perovskite film, (a) without and (b) with 6% SrBr₂.

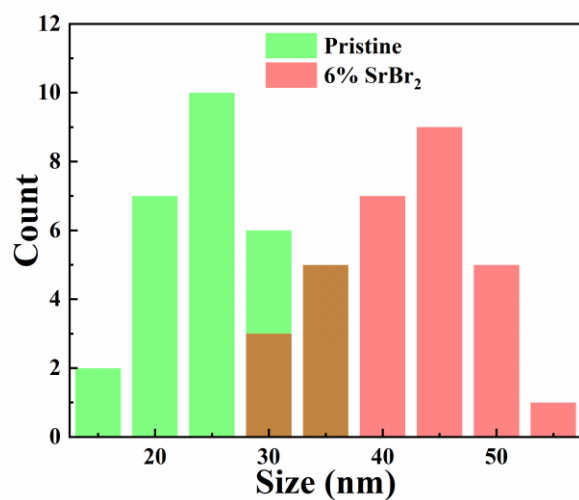


Figure S6. The histogram of grain size distribution.

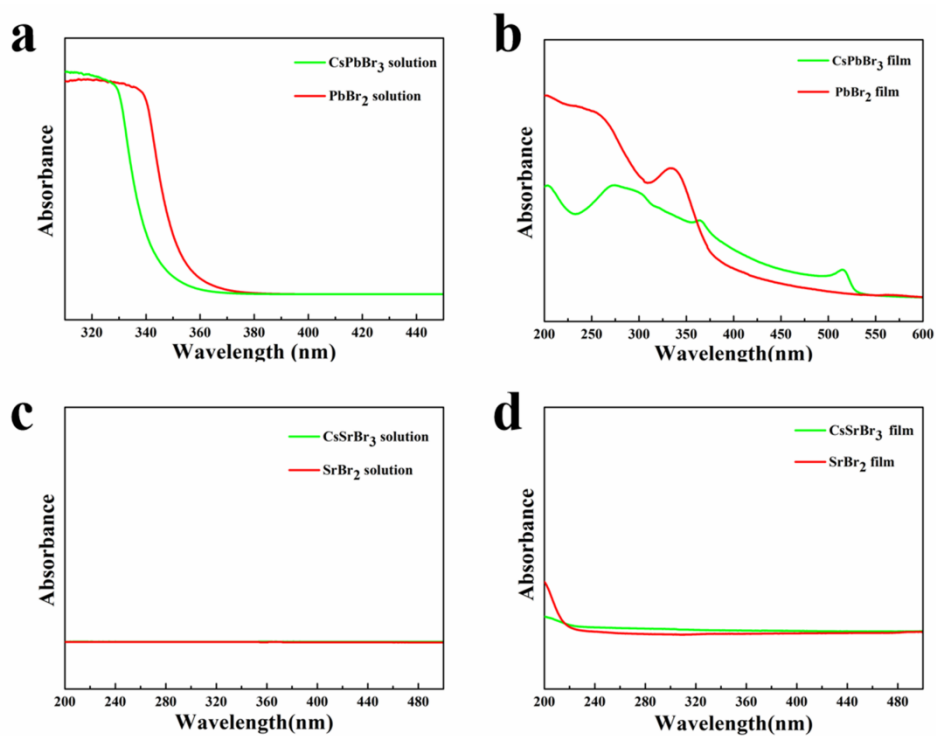


Figure S7. Absorption spectra of (a) CsPbBr₃ and PbBr₂ in DMSO, (b) CsPbBr₃ film and PbBr₂ film, (c) CsSrBr₃ and SrBr₂ in DMSO, (d) CsSrBr₃ film and SrBr₂ film.

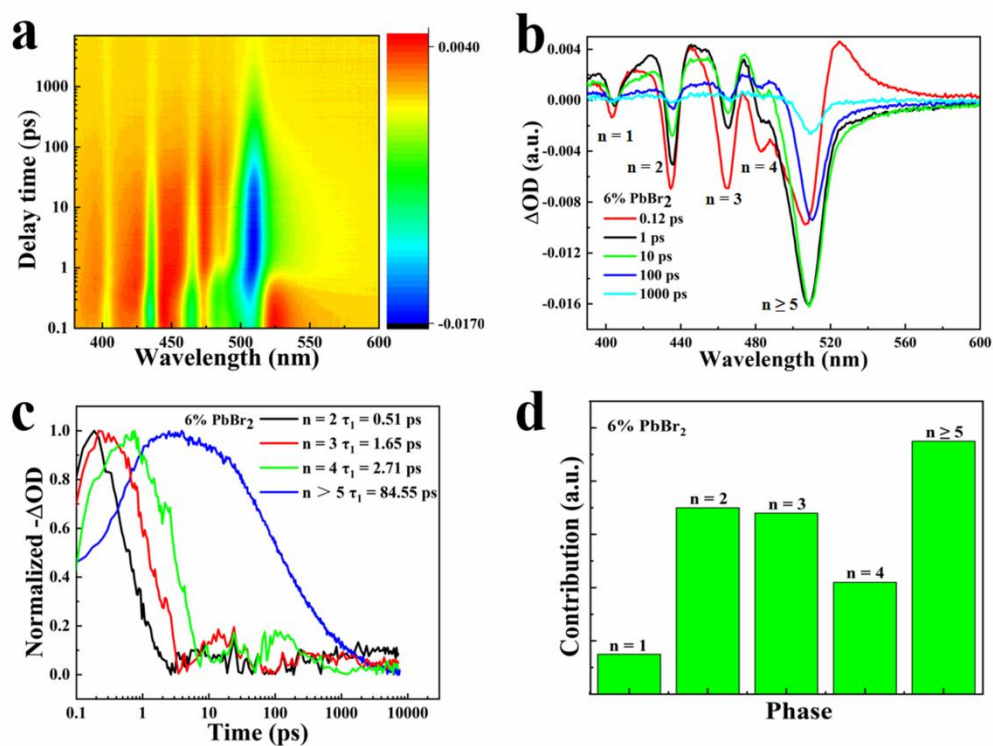


Figure S8. (a) TA spectra, (b) TA spectra at selected timescales, (c) TA traces as a function of time and extracted fast component decay constants (τ_1) for different phases, (d) Relative contents of different phases for quasi-2D perovskite films with 6% PbBr₂, the relative contents were obtained according to the amplitude of GSBs in TA spectra at 0.12 ps.

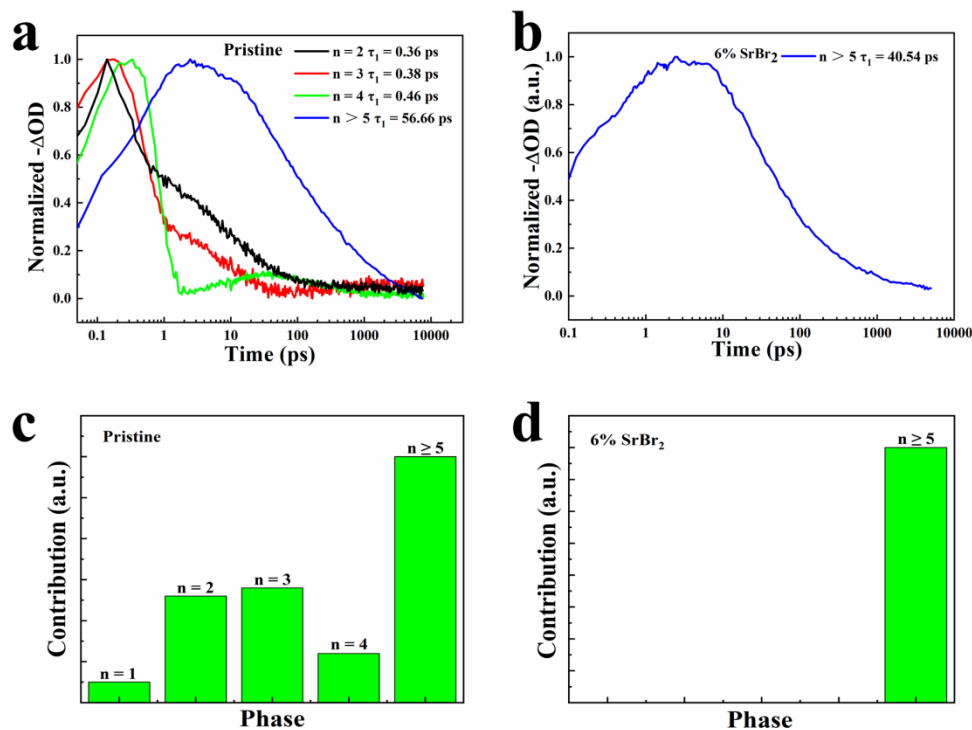


Figure S9. TA traces as a function of time and extracted fast component decay constants (τ_1) for different phases (a) without and (b) with 6% SrBr₂. Relative contents of different phases for quasi-2D perovskite films (c) without and (d) with 6% SrBr₂, the relative contents obtained according to the amplitude of GSBs in TA spectra at 0.12 ps.

	τ_{au} (ns)	τ_1 (ns)	A ₁	τ_2 (ns)	A ₂	τ_3 (ns)	A ₃
Pristine	26.2	8.0	39%	52.0	44%	1.4	17%
6% PbBr₂	16.0	1.3	23%	6.4	43%	38.2	34%
6% SrBr₂	39.5	13.3	39%	68.0	50%	2.6	11%

Figure S10. TRPL fitting data of perovskite films without additive, with 6% PbBr₂ and with 6% SrBr₂, respectively.

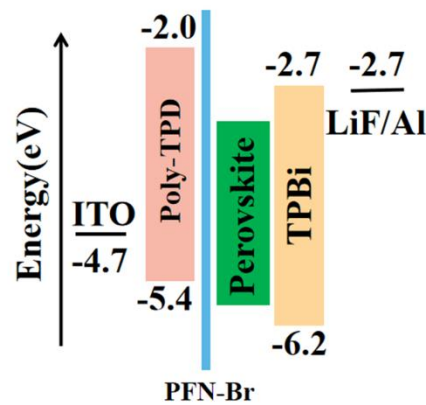


Figure S11. Energy level diagram of the PeLED device structure.

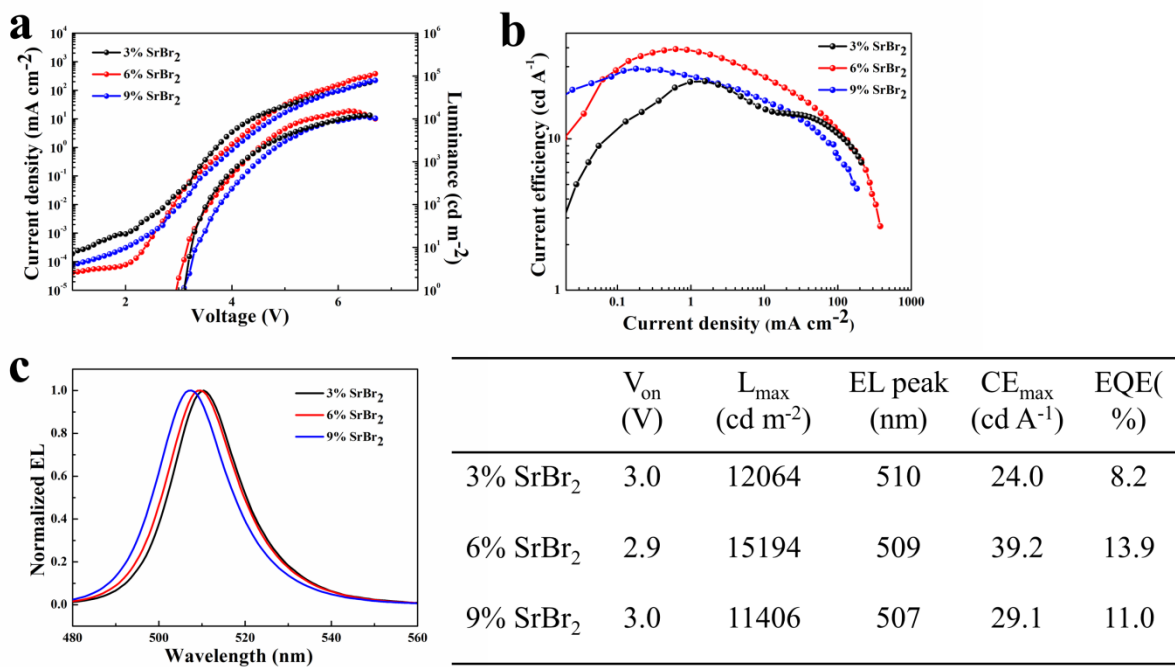


Figure S12. (a) Current density–voltage–luminance, (b) current efficiency–current density curves, and (c) EL spectra of PeLEDs with different SrBr₂ proportions.

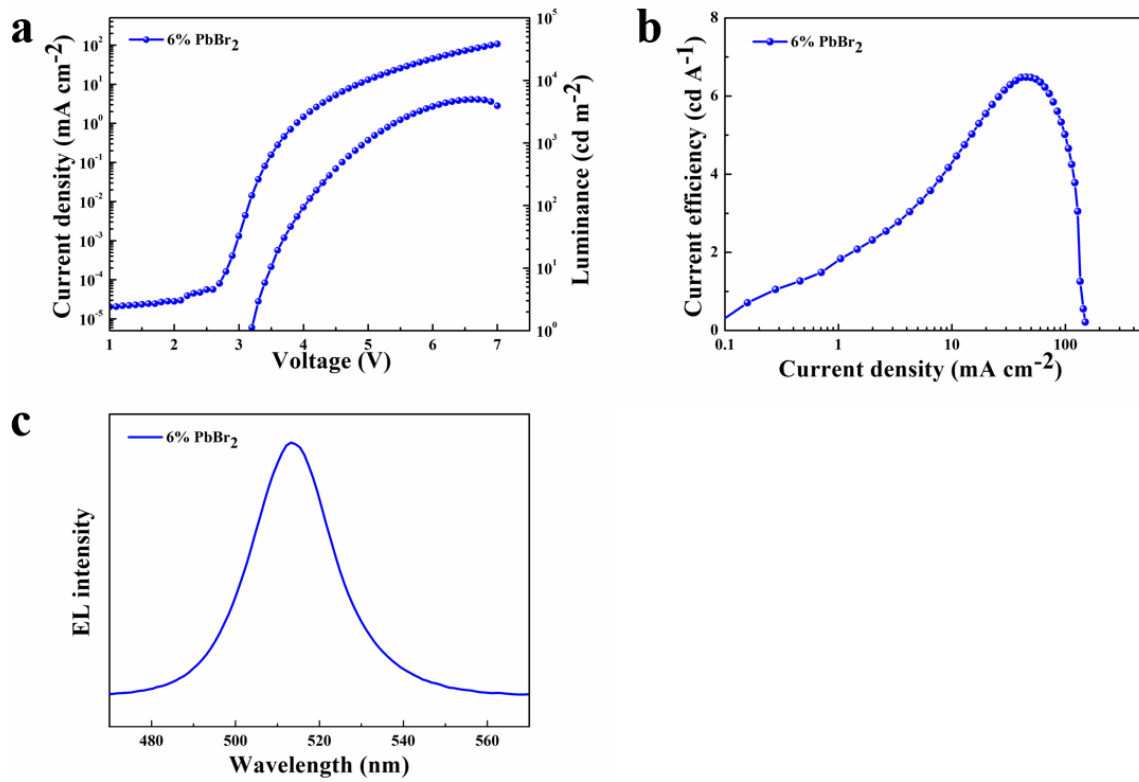


Figure S13. (a) Current density–voltage–luminance, (b) current efficiency–current density curves, and (c) EL spectra of PeLEDs with 6% PbBr₂.

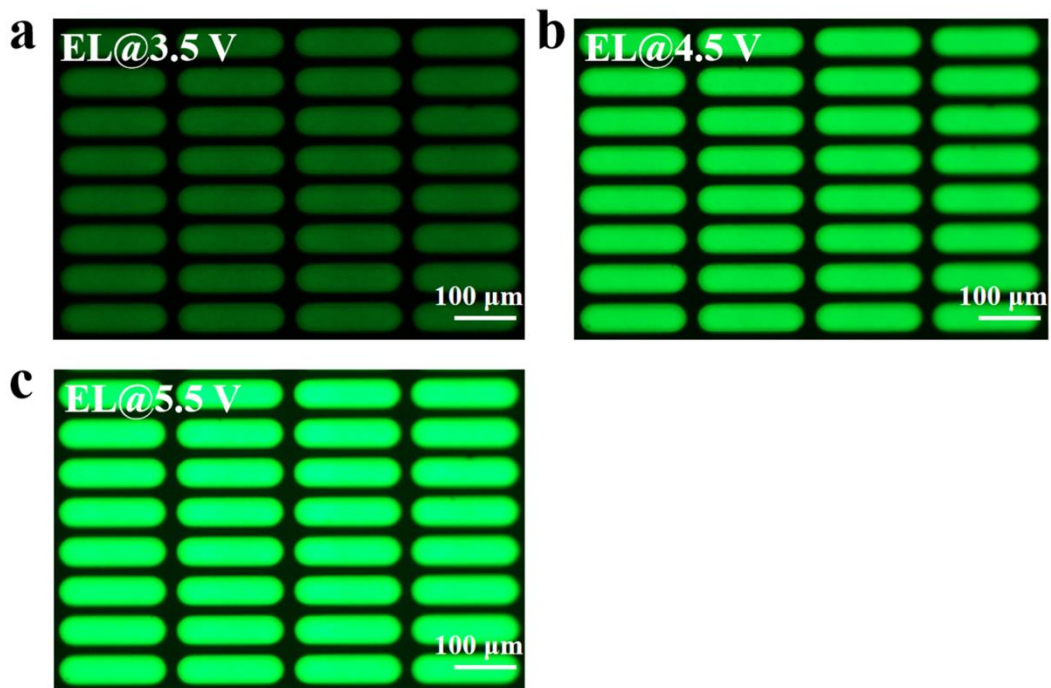


Figure S14. (a-c) EL images of perovskite film pixel under a driven voltage of 3.5V, 4.5V, and 5.5 V, respectively.

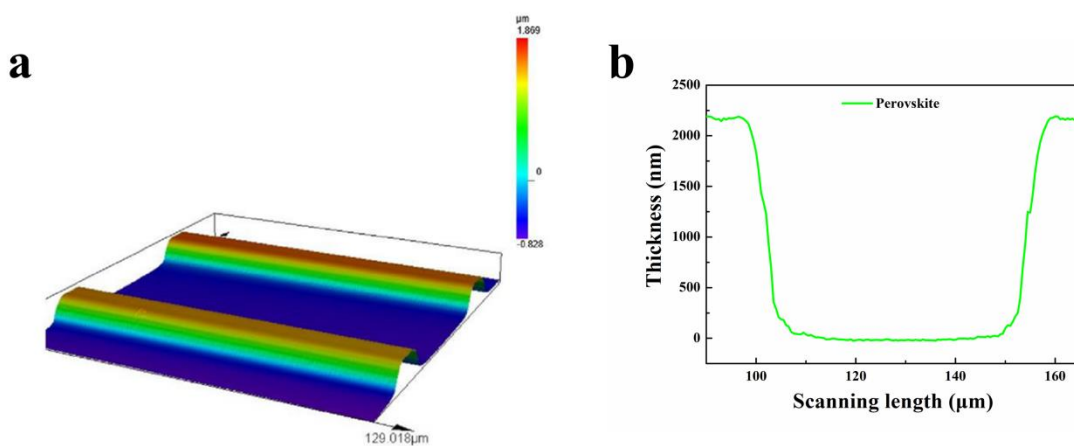


Figure S15. (a, b) The confocal images of perovskite film.

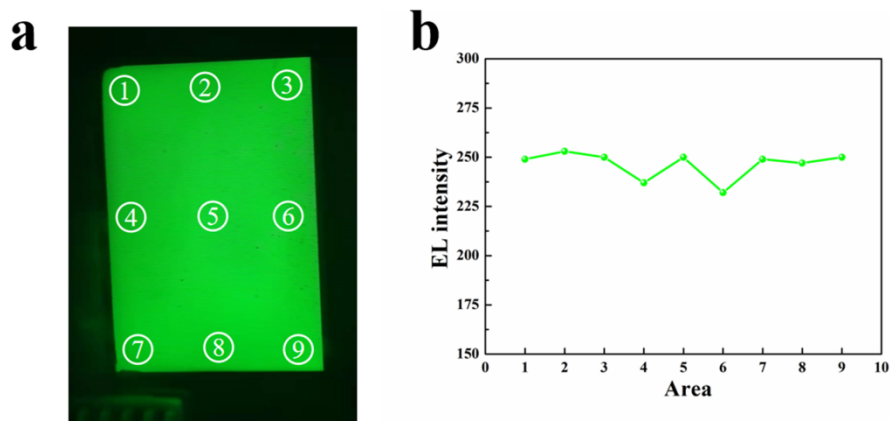


Figure S16. (a) Photo of a working PeLED device operated under voltage of 4.5 V with an active area of 10.0 cm², (b) EL intensity curves of the selected micro-areas marked in (a).

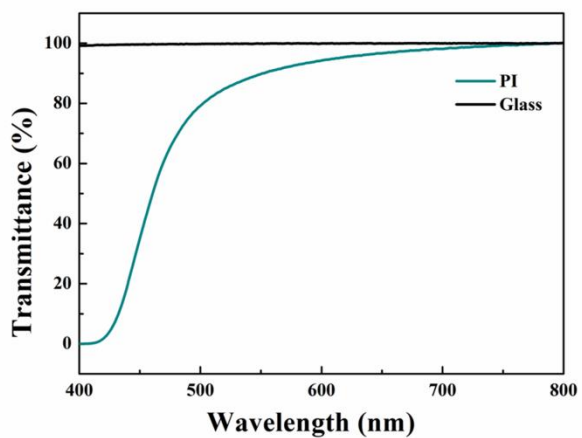


Figure S17. Transmittance of glass and PI substrates.

Table S1. Comparison of device performances for PeLEDs based on ink-jet printing technology reported to date.

Type of Perovskites	Substrate type	Wavelength (nm)	Peak EQE (%)	Area (cm ²)	References
Nanocrystal	Patterned	520	2.8	0.1	1
Nanocrystal	Patterned	515	3.03	0.04	2
3D	W/O Patterned	530	-	0.04	3
Quasi-2D	W/O Patterned	518	9.0	0.09	4
Nanocrystal	W/O Patterned	517	8.54	0.04	5
3D	W/O Patterned	535	2.01 cd A ⁻¹	-	6
Quasi-2D	Patterned	645	3.5	0.1	7
		515	3.4		
		486	1.0		
Nanocrystal	Patterned	646	9.6	0.1	8
Quasi-2D	Patterned	511	10.1	0.1	9
Quasi-2D	Patterned	509	13.9	0.1	This work
			9.3	10.0	

References

- [1] D. Li, J. Wang, M. Li, G. Xie, B. Guo, L. Mu, H. Li, J. Wang, H.-L. Yip, J. Peng. *Adv. Mater. Technol.* **2020**, *5*, 2000099.
- [2] C. Zheng, X. Zheng, C. Feng, S. Ju, Z. Xu, Y. Ye, T. Guo, F. Li. *Organic Electronics.* **2021**, *93*, 106168.
- [3] F. Hermerschmidt, F. Mathies, V. R. F. Schröder, C. Rehermann, N. Z. Morales, E. L. Unger, E. J. W. List-Kratochvil. *Mater. Horiz.* **2020**, *7*, 1773.
- [4] Y. Li, Z. Chen, D. Liang, J. Zang, Z. Song, L. Cai, Y. Zou, X. Wang, Y. Wang, P. Li, X. Gao, Z. Ma, X. Mu, A. El-Shaer, L. Xie, W. Su, T. Song, B. Sun. *Adv. Optical. Mater.* **2021**, *6*, 2100553.
- [5] C. Wei, W. Su, J. Li, B. Xu, Q. Shan, Y. Wu, F. Zhang, M. Luo, H. Xiang, Z. Cui, H. Zeng. *Adv. Mater.* **2022**, *34*, 2107798.
- [6] J. Zhao, L.-W. Lo, H. Wan, P. Mao, Z. Yu, C. Wang. *Adv. Mater.* **2021**, *33*, 2102095.

- [7] J. Wang, D. Li, L. Mu, M. Li, Y. Luo, B. Zhang, C. Mai, B. Guo, L. Lan, J. Wang, H.-L. Yip, J. Peng. *ACS Appl. Mater. Interfaces* **2021**, *13*, 41773.
- [8] D. Li, J. Wang, M. Li, B. Guo, L. Mu, Y. Luo, Y. Xiao, C. Mai, J. Wang, J. Peng. *Mater. Futures* **2022**, *1*, 015301.
- [9] J. Wang, D. Li, Y. Luo, J. Wang, J. Peng. *Adv. Mater. Technol.* **2022**, 2200370. DOI: 10.1002/admt.202200370.